

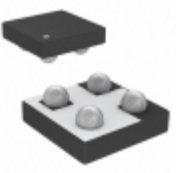
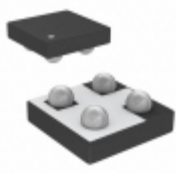
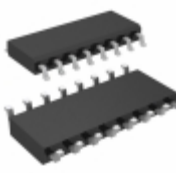



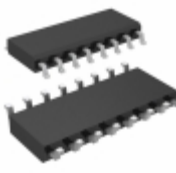
	<h2>SI8413DB-T1-E1</h2>
	<p>Hersteller-Teilenummer: SI8413DB-T1-E1</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 4.8A 2X2 4-MFP</p> <p>Datenblätter:  SI8413DB-T1-E1.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 531430 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI8413DB-T1-E1
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 20V 4.8A 2X2 4-MFP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	531430 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	4-XFBGA, CSPBGA
Supplier Device-Gehäuse	4-Microfoot
Verlustleistung (max)	1.47W (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.8A (Ta)
Rds On (Max) @ Id, Vgs	48 mOhm @ 1A, 4.5V
VGS (th) (Max) @ Id	1.4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	21nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)



















































SI8413DB-T1-E1 ist neu im Original, Suche SI8413DB-T1-E1 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI8413DB-T1-E1 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI8413DB-T1-E1: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI8415DB-T1 VISHAY SI8415DB-T1 VISHAY</p>	 <p>SI8413DB-T1-E1 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 4.8A 2X2 4-MFP</p>	 <p>SI8415DB-T1-E1 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 5.3A 2X2 4-MFP</p>	 <p>SI8410BD-D-IS Energy Micro (Silicon Labs) DGTL ISO 5KV 1CH GEN PURP 16SOIC</p>
 <p>SI8413DB-T1-E3 VISHAY VISHAY MFP</p>	 <p>SI8416DB-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 8V 16A MICRO</p>	 <p>SI8410DB-T2-E1 Electro-Films (EFI) / Vishay MOSFET N-CH 20V MICROFOOT</p>	 <p>SI8410BD-D-ISR Energy Micro (Silicon Labs) DGTL ISO 5KV 1CH GEN PURP 16SOIC</p>

heiße Teile

Mehr

 SI8401DB-T1	 SI8401DB-T1-E1	 SI8401DB-T1-E1	 SI8401DB-T1-E3	 SI8401DB-T1-E3
 SI8402DB-T1	 SI8402DB-T1-E1	 SI8402DB-T1-E1	 SI8402DB-T1-E1.	 SI8402DB-T1-E3
 SI8404DB-T1-E1	 SI8404DB-T1-E1	 SI8405DB	 SI8405DB-T1	 SI8405DB-T1-E1
 SI8405DB-T1-E1	 SI8405DB-T1-E3	 SI8405DB-T1-E3	 SI8409DB-T1	 SI8409DB-T1-E1
 SI8409DB-T1-E1	 SI8410AB	 SI8410BB-D-ISR	 SI8410BB-I-DS	 SI8413DB-T1-E1
 SI8415DB-T1	 SI8415DB-T1-E1	 SI8415DB-T1-E1	 SI8417DB-T2-E1	 SI8417DB-T2-E1
 SI8420BB	 SI8420BB-D-IS	 SI8421AB-D-ISR	 SI8422AB-D-ISR	 SI8422BD
 SI8424DB-T1-E1	 SI8424DB-T1-E1	 SI8425DB-T1-E1	 SI8425DB-T1-E1	 SI8429DB-T1-E1
 SI8429DB-T1-E1	 SI8430-A-IS	 SI8430-BIS	 SI8430-C-IS	 SI8430AB-D-IS
 SI8430AB-D-ISR	 SI8430BB-C-IS	 SI8430BB-D-IS	 SI8431-A-IS	 SI8431-BIS

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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